
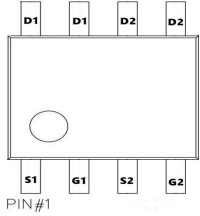
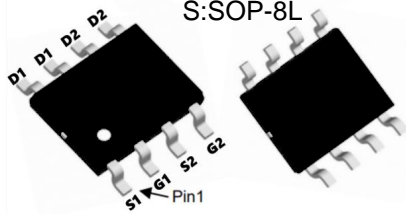
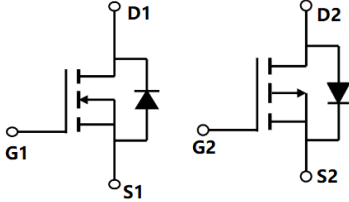


**TM06G02S**

**N+P-Channel Enhancement Mode Mosfet**

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>• Low <math>R_{DS(ON)}</math></li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>• Load switch</li> <li>• PWM</li> </ul>	<p><b>Product Summary</b></p> <p><b>N Channel</b>  <math>V_{DS} = 20V, I_D = 6.0A</math>  <math>R_{DS(ON)} = 21m\Omega (typ.) @ V_{GS} = 4.5V</math></p> <p><b>P Channel</b>  <math>V_{DS} = -20V, I_D = -5.0A</math>  <math>R_{DS(ON)} = 52m\Omega (typ.) @ V_{GS} = 4.5V</math></p> <p>100% UIS Tested                  100% <math>R_g</math> Tested</p> 
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Marking: 06G02 OR 4606B

**Absolute Maximum Ratings ( $T_C = 25^\circ C$  unless otherwise noted)**

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
$V_{DS}$	Drain-Source Voltage	20	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	$\pm 12$	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6	-5	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5	-4	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	20	-12	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	72	59	mJ
$I_{AS}$	Avalanche Current	21	-19	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation <sup>4</sup>	2.5	2.08	W
$T_{STG}$	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	50	$^\circ C/W$

**TM06G02S**
**N+P-Channel Enhancement Mode Mosfet**
**N-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.7	1	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance note2	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	21	27	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3A	-	29	44	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHz	-	358	-	pF
C <sub>oss</sub>	Output Capacitance		-	69.3	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	58.5	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =10V, I <sub>D</sub> =2A, V <sub>GS</sub> =4.5V	-	5.6	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	0.8	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	1	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =10V, I <sub>D</sub> =4A, R <sub>GEN</sub> =3Ω, V <sub>GS</sub> =4.5V	-	5	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	30	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	48	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	36	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	6	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =4A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

P-Channel Electrical Characteristics ( $T_J=25\text{ }^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-20	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-20V, V_{GS}=0V,$	-	-	-1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5	-0.7	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=-4.5V, I_D=-3A$	-	52	70	m $\Omega$
		$V_{GS}=-2.5V, I_D=-2A$	-	70	100	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=-10V, V_{GS}=0V,$ $f=1.0MHz$	-	503	-	pF
$C_{oss}$	Output Capacitance		-	67	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	58	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=-10V, I_D=-2A,$ $V_{GS}=-4.5V$	-	4.1	-	nC
$Q_{gs}$	Gate-Source Charge		-	0.8	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	1.1	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=-10V, I_D=-3A,$ $R_G=1\Omega, V_{GEN}=-4.5V,$ $R_L=1.2\Omega$	-	11	-	ns
$t_r$	Turn-on Rise Time		-	52	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	16	-	ns
$t_f$	Turn-off Fall Time		-	10	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	-5	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-12	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=-3A$	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature  
 2. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$

## Typical Performance Characteristics

### N-Channel Typical Characteristics

Figure 1: Output Characteristics

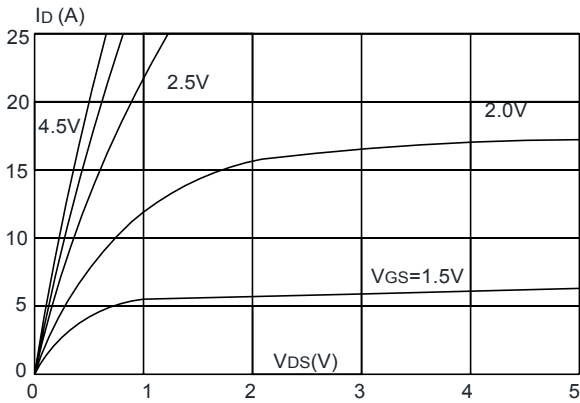


Figure 2: Typical Transfer Characteristics

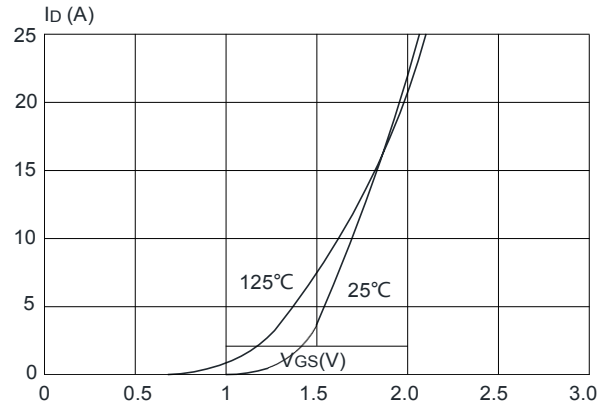


Figure 3: On-resistance vs. Drain Current

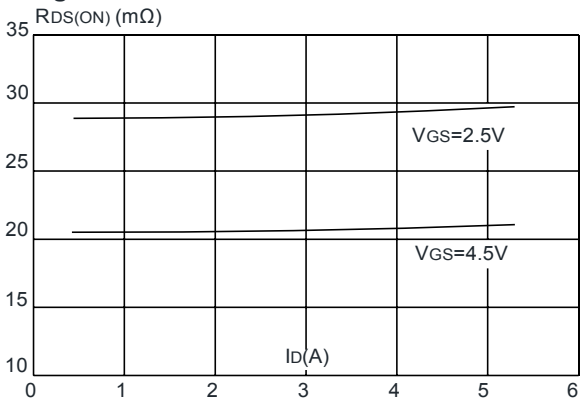


Figure 4: Body Diode Characteristics

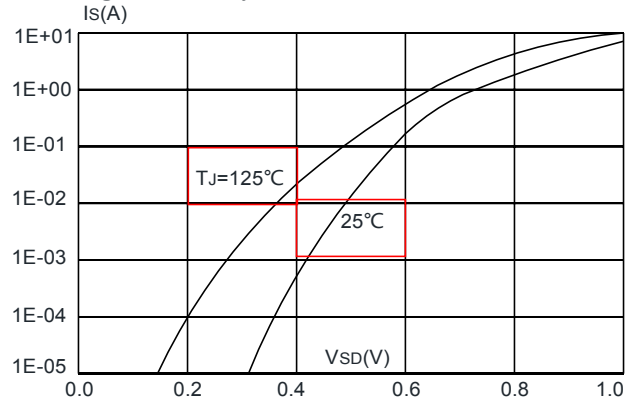


Figure 5: Gate Charge Characteristics

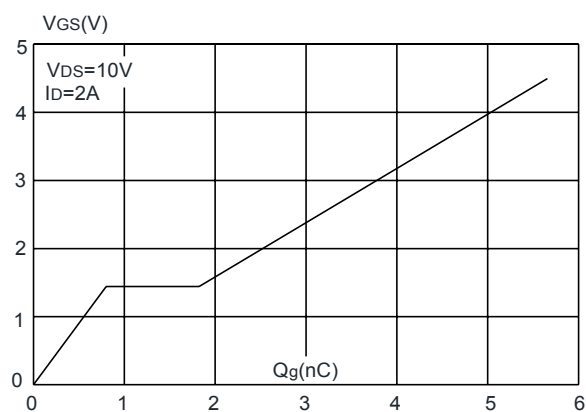
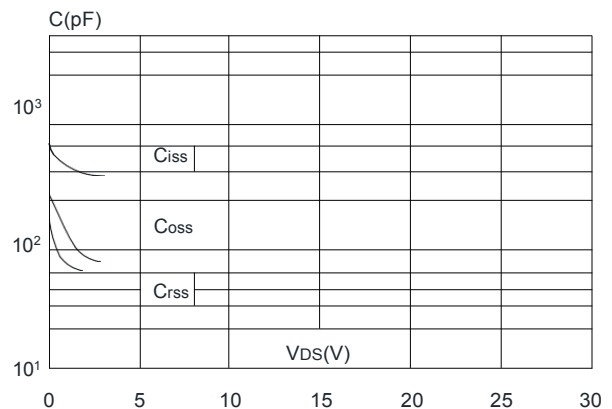


Figure 6: Capacitance Characteristics



## Typical Performance Characteristics

### P-Channel Typical Characteristics

Figure 1: Output Characteristics

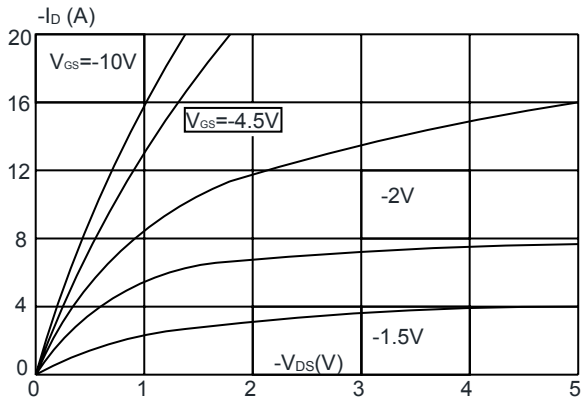


Figure 2: Typical Transfer Characteristics

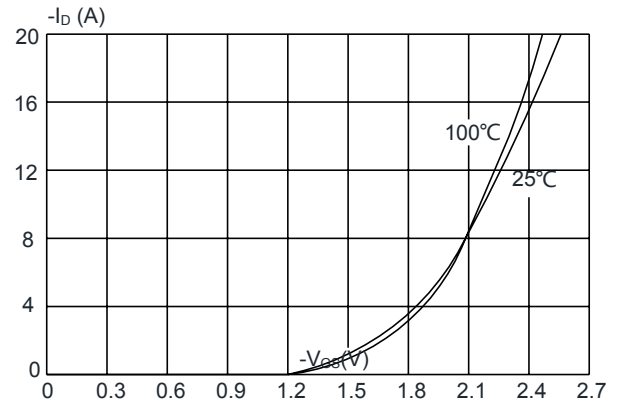


Figure 3: On-resistance vs. Drain Current

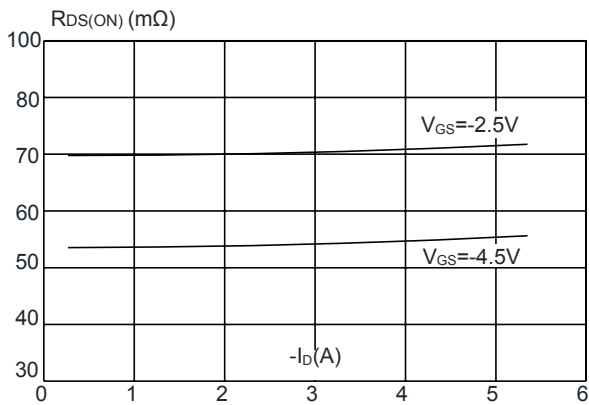


Figure 4: Body Diode Characteristics

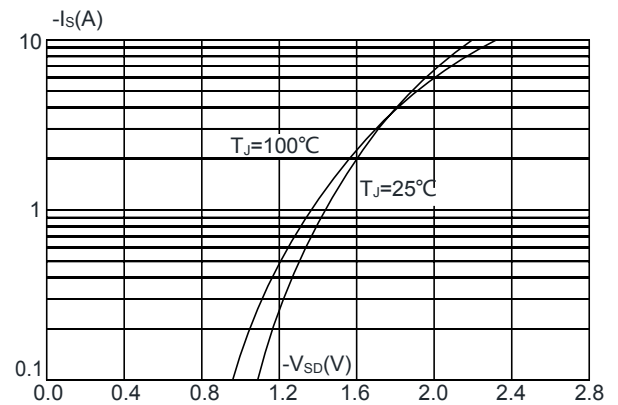


Figure 5: Gate Charge Characteristics

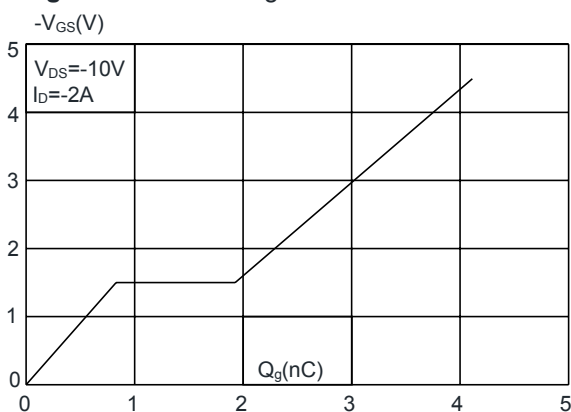
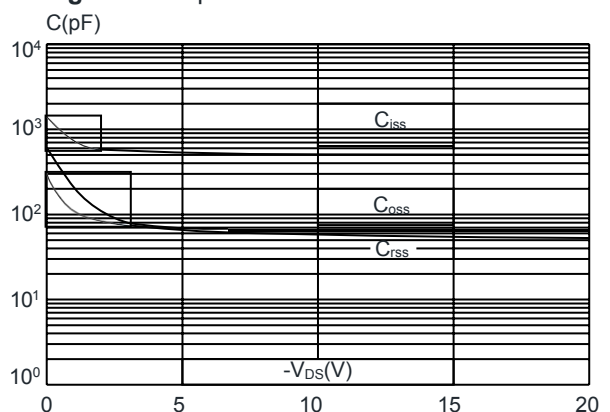
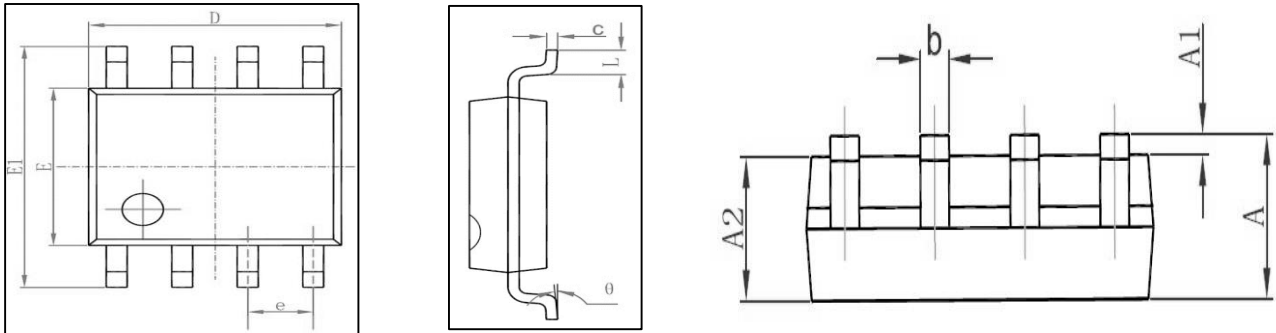


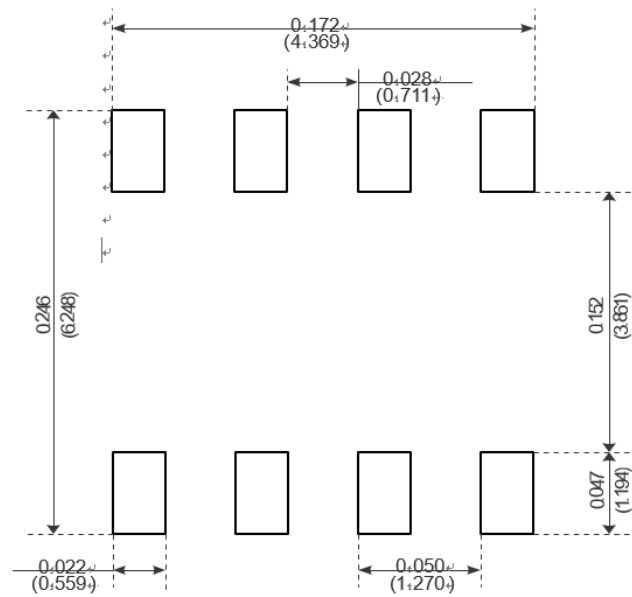
Figure 6: Capacitance Characteristics



## Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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